N-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.0075 at V_{GS} = 10 V	75[a]
	0.0085 at V_{GS} = 4.5 V	

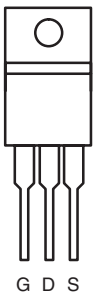
FEATURES

- 175 °C Rated Maximum Junction Temperature

Available

RoHS*
COMPLIANT

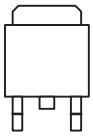
TO-220AB



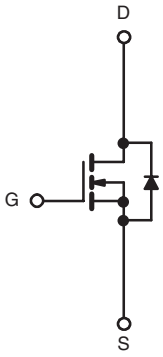
Top View
SUP75N06-07L

DRAIN connected to TAB

TO-263



Top View
SUB75N06-07L



N-Channel MOSFET

Ordering Information: SUB75N06-07L (TO-263)
SUB75N06-07L-E3 (TO-263, Lead (Pb)-free)
SUP75N06-07L (TO-263)
SUP75N06-07L-E3 (TO-263, Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	75[a]	A
	T_C = 125 °C		55	
Pulsed Drain Current		I_{DM}	240	
Avalanche Current		I_{AS}	60	
Single Pulse Avalanche Energy[b]	L = 0.1 mH	E_{AS}	280	mJ
Power Dissipation	T_C = 25 °C (TO-220AB and TO-263)	P_D	250[c]	W
	T_A = 25 °C (TO-263)[d]		3.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Limit**	**Unit**
Junction-to-Ambient	PCB Mount (TO-263)[d]	R_{thJA}	40	°C/W
	Free Air (TO-220AB)		62.5	
Junction-to-Case		R_{thJC}	0.6	

Notes:
a. Package limited.
b. Duty cycle ≤ 1 %.
c. See SOA curve for voltage derating.
d. When Mounted on 1" square PCB (FR-4 material).

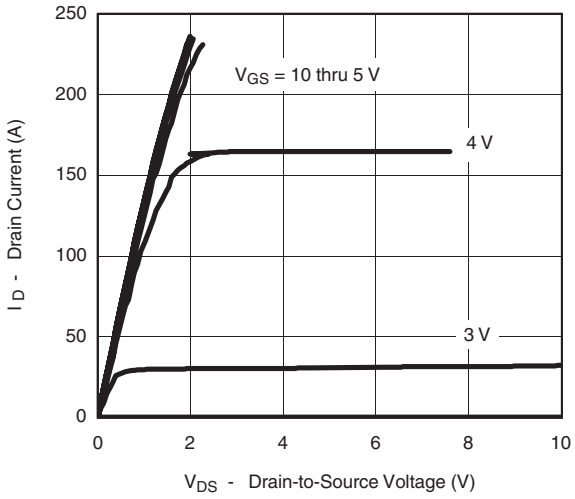
* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.0		3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.0061	0.0075	Ω
		V_{GS} = 4.5 V, I_D = 20 A		0.0071	0.0085	
		V_{GS} = 10 V, I_D = 30 A, T_J = 125 °C			0.012	
		V_{GS} = 10 V, I_D = 30 A, T_J = 175 °C			0.015	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	30			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		6300		pF
Output Capacitance	C_{oss}			920		
Reverse Transfer Capacitance	C_{rss}			350		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 75 A		75	120	nC
Gate-Source Charge[c]	Q_{gs}			18		
Gate-Drain Charge[c]	Q_{gd}			27		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.47 Ω $I_D \cong$ 75 A, V_{GEN} = 10 V, R_G = 2.5 Ω		14	40	ns
Rise Time[c]	t_r			15	40	
Turn-Off Delay Time[c]	$t_{d(off)}$			150	300	
Fall Time[c]	t_f			50	100	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				75	A
Pulsed Current	I_{SM}				240	
Forward Voltage[a]	V_{SD}	I_F = 75 A, V_{GS} = 0 V		1.0	1.3	V
Reverse Recovery Time	t_{rr}	I_F = 75 A, di/dt = 100 A/µs		67	120	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			6	8	A
Reverse Recovery Charge	Q_{rr}			0.2	0.48	µC

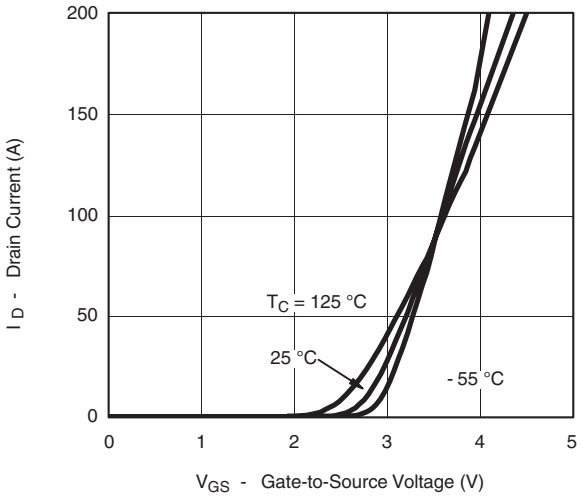
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

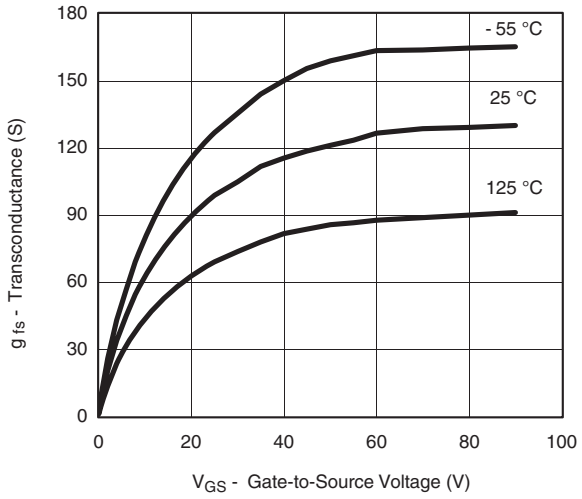
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



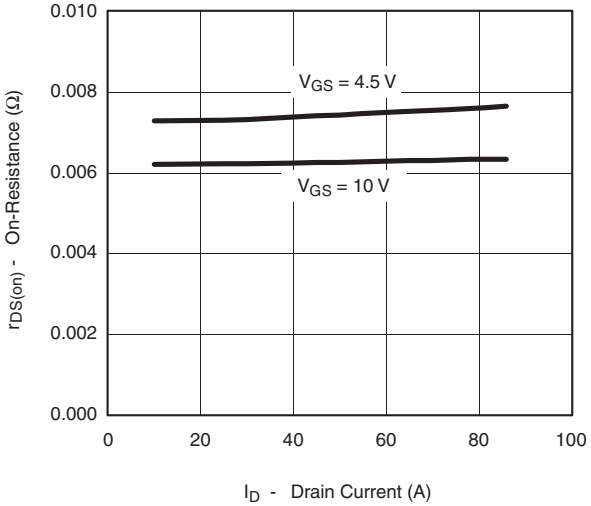
Output Characteristics



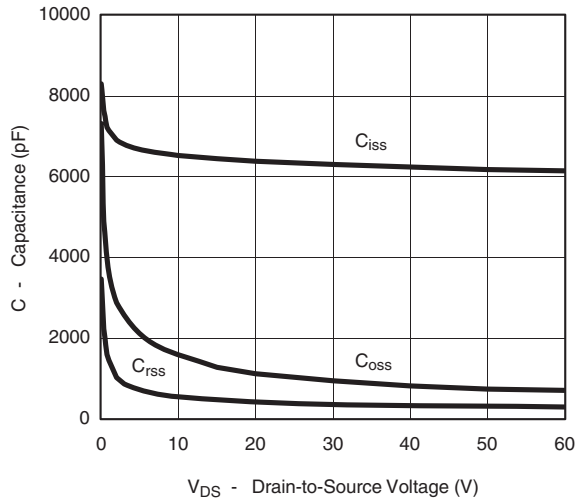
Transfer Characteristics



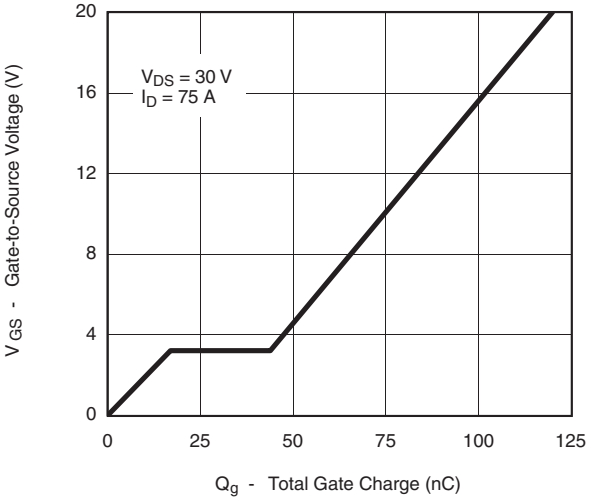
Transconductance



On-Resistance vs. Drain Current

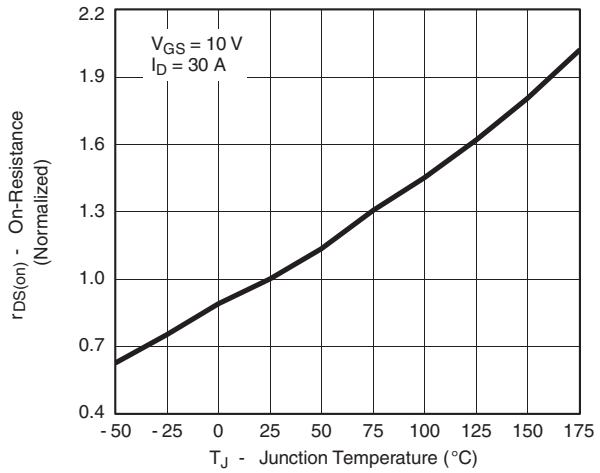


Capacitance

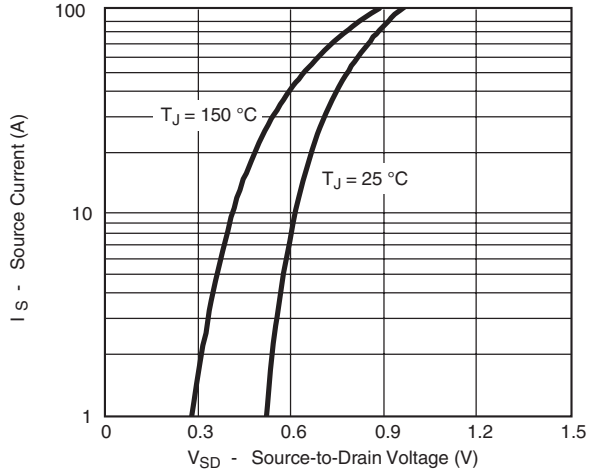


Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

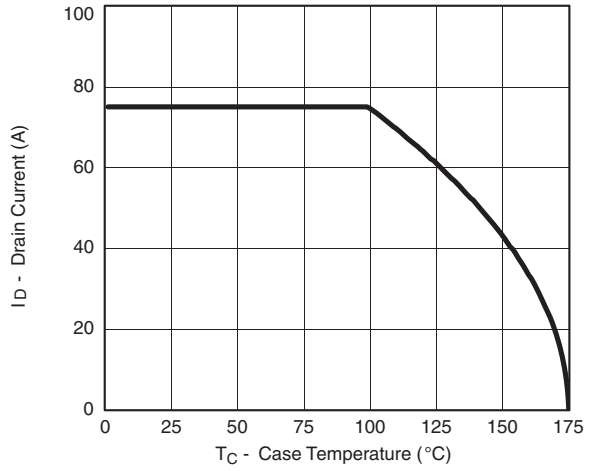


On-Resistance vs. Junction Temperature

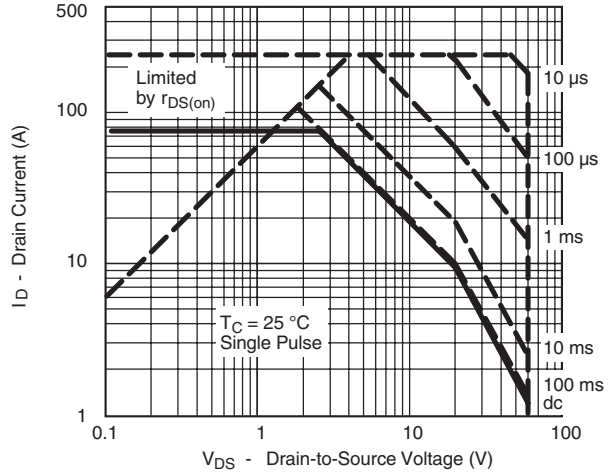


Source-Drain Diode Forward Voltage

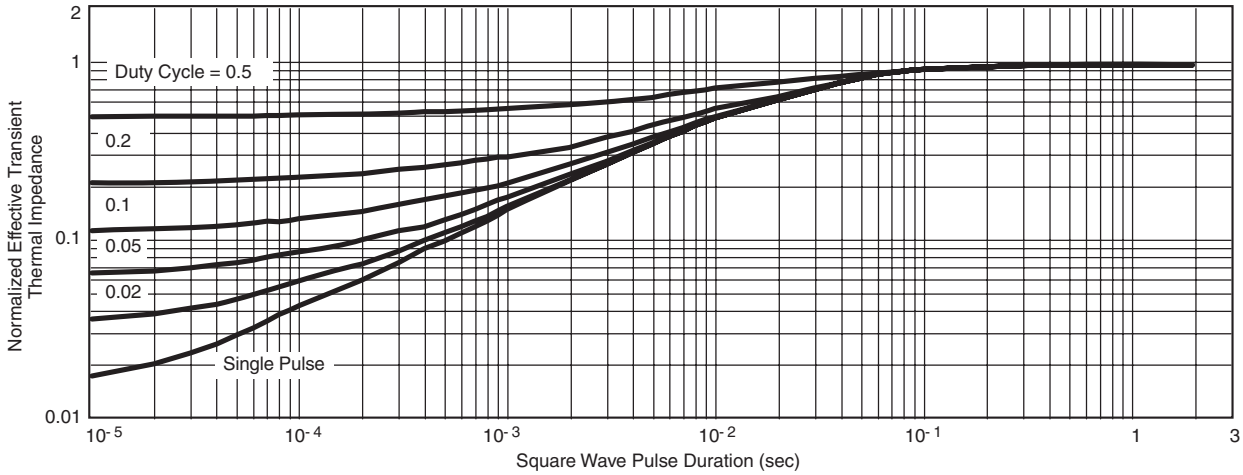
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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